Electronic Supplementary Material (ESI) for Journal of Materials Chemistry A.

Supplementary information for

Schottky Contact of Artificial Polymer Semiconductor Composed of Poly(dimethylsiloxane) and Multiwall Carbon Nanotube

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1. A comparison of Schottky barrier heights of this work with some previous results

Table S1 Schottky barrier heights of Al/composite junctions

Metal	Composite Semiconductor	SBH (eV)	Ref.
Al	SWNT-Poly(ethylene glycol dimethacrylate-n-vinyl imidazole)	0.61	S1
Al	FWNT-PEDOT	0.72	S2
Al	MWNT-PDMS	0.95	This work

References:

S1. M. A. Afrailov, A. Kara, N. Tekin, S. Beyaz and H. Köçkar, *Thin Solid Films*, 2012, **520**, 2106-2109.

S2. B. Gupta, M. Mehta, A. Melvin, R. Kamalakannan, S. Dash, M. Kamruddin and A. K. Tyagi, *Mater. Chem. Phys.*, 2014, **147**, 867-877.